

FIG. 1

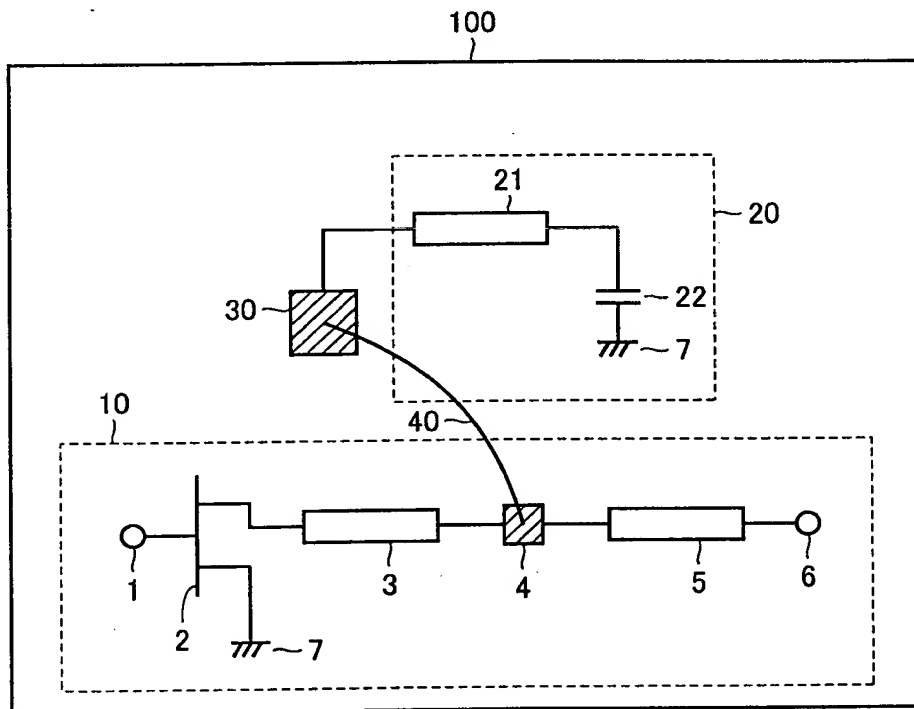


FIG. 2

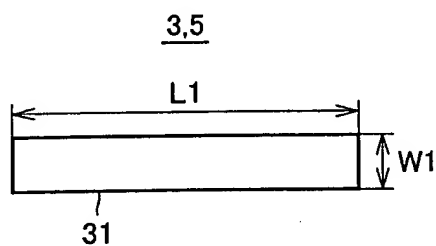


FIG. 3

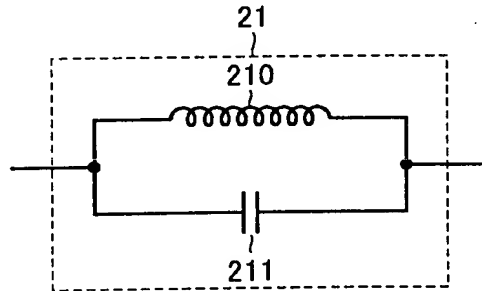


FIG. 4

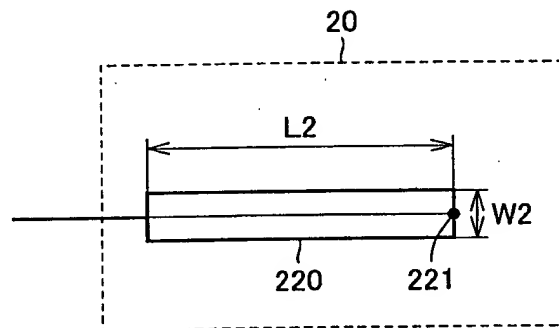


FIG. 5

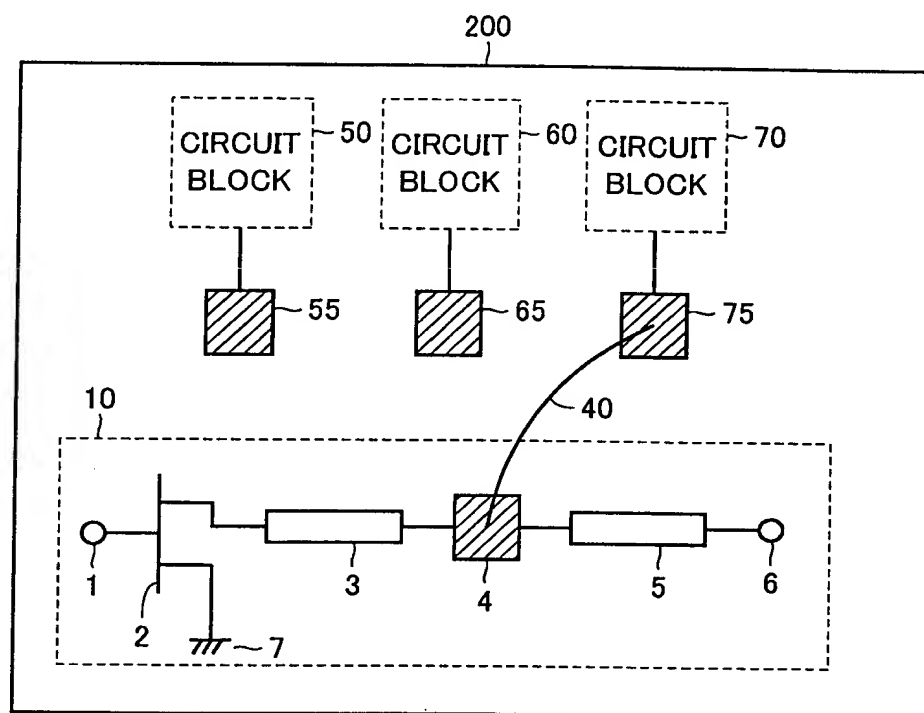
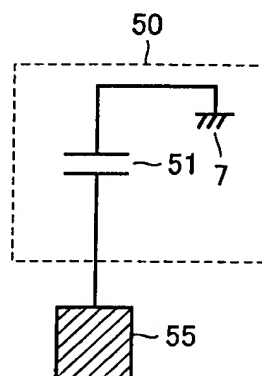


FIG. 6



Title: HIGH-FREQUENCY SEMICONDUCTOR INTEGRATED CIRCUIT CAPABLE OF SWITCHING
BETWEEN CHARACTERISTICS THE OF

Inventors: KANAYA ET AL.

Atty Docket No.: 401407

Leydig, Voit & Mayer, Ltd. 202-737-6770

FIG. 7

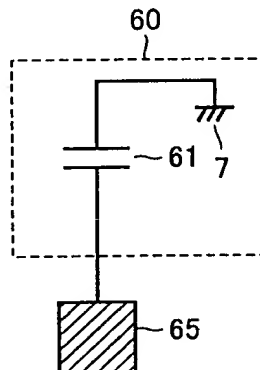


FIG. 8

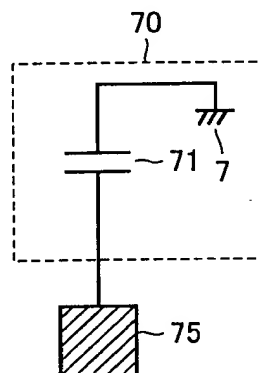


FIG. 9

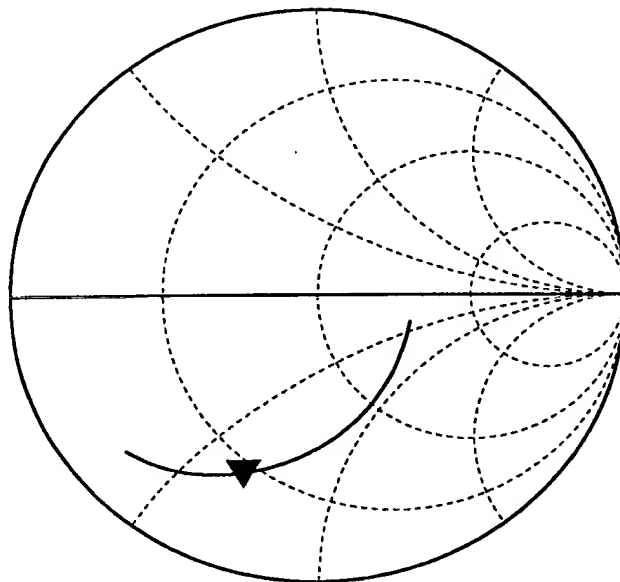


FIG. 10

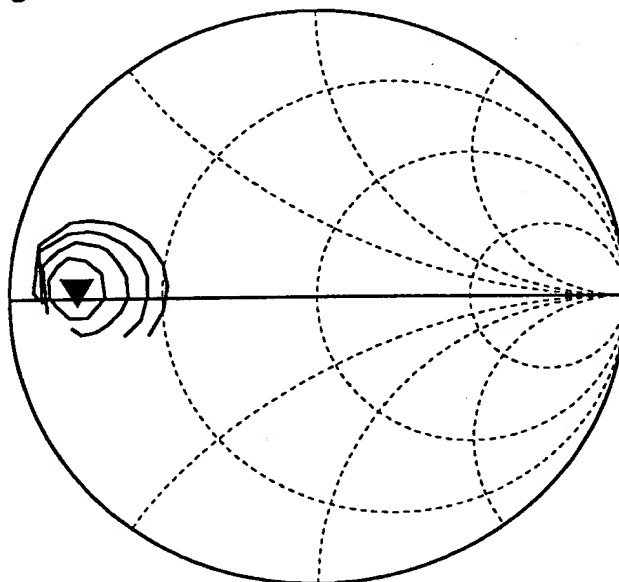


FIG. 11

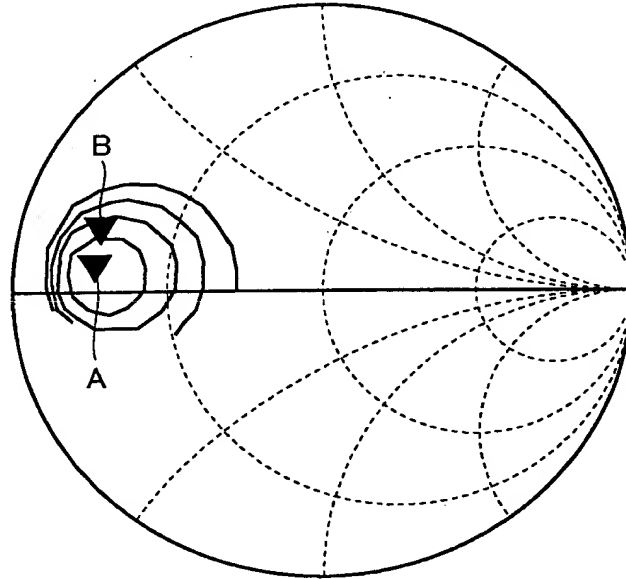


FIG. 12

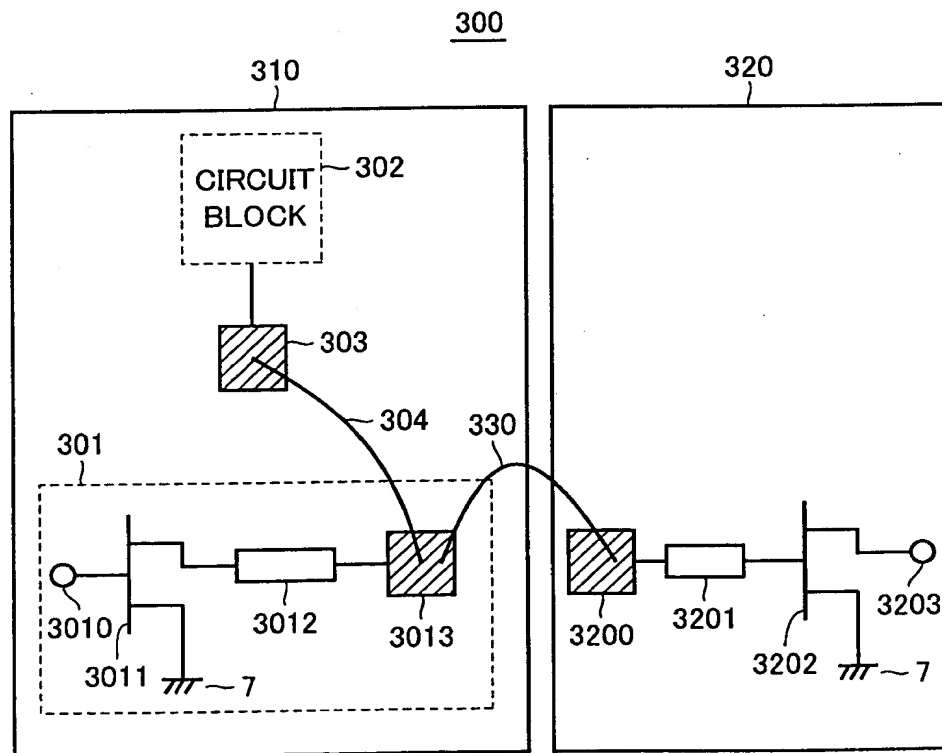


FIG. 13A

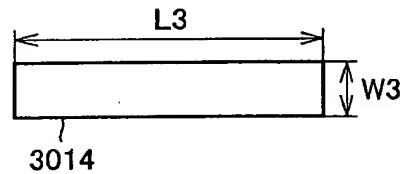


FIG. 13B

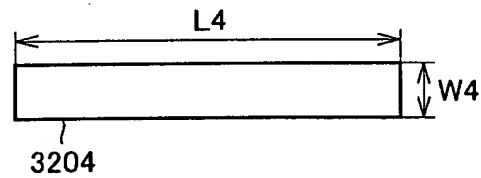


FIG. 14

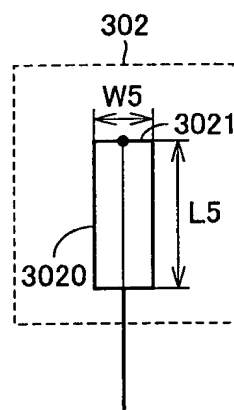


FIG. 15

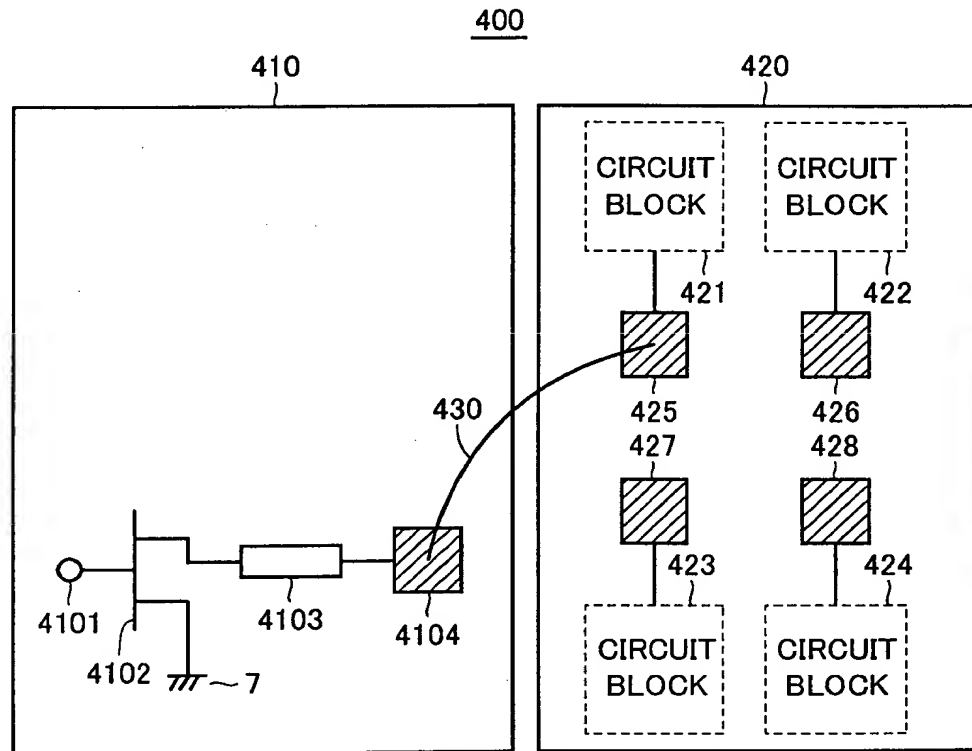


FIG. 16

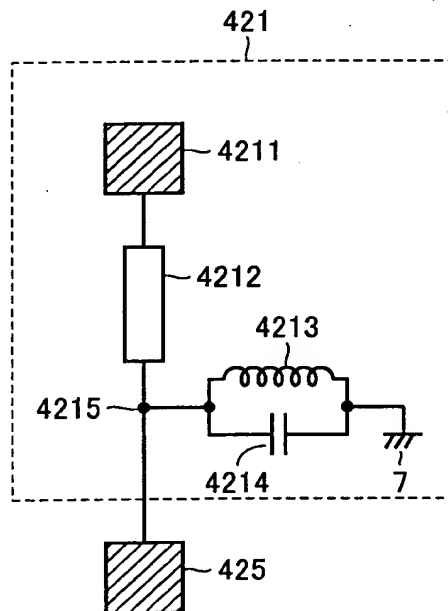


FIG. 17

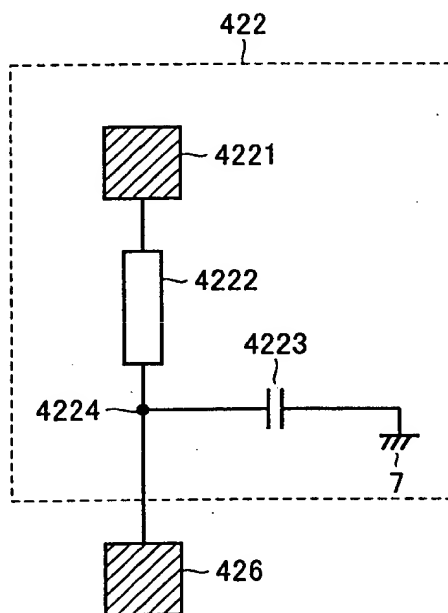


FIG. 18

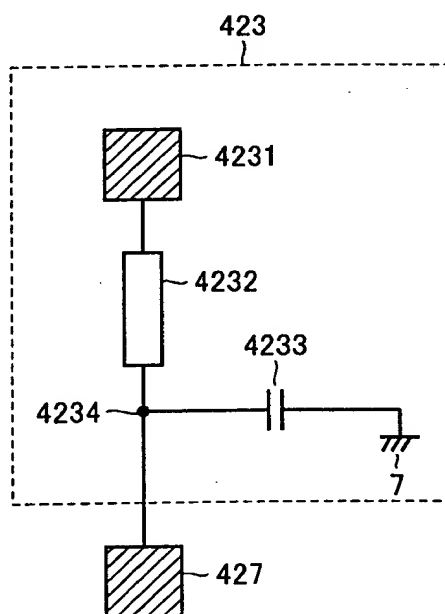


FIG. 19

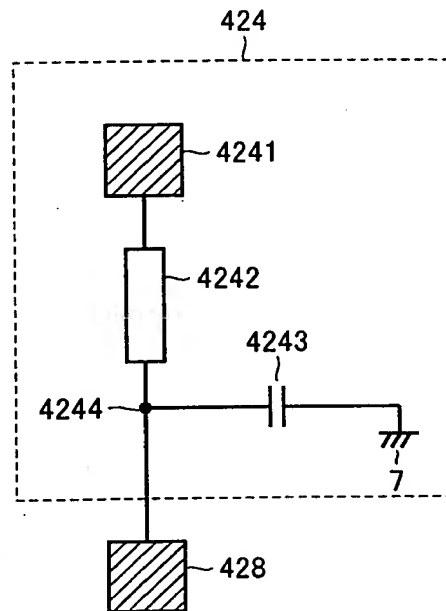


FIG. 20

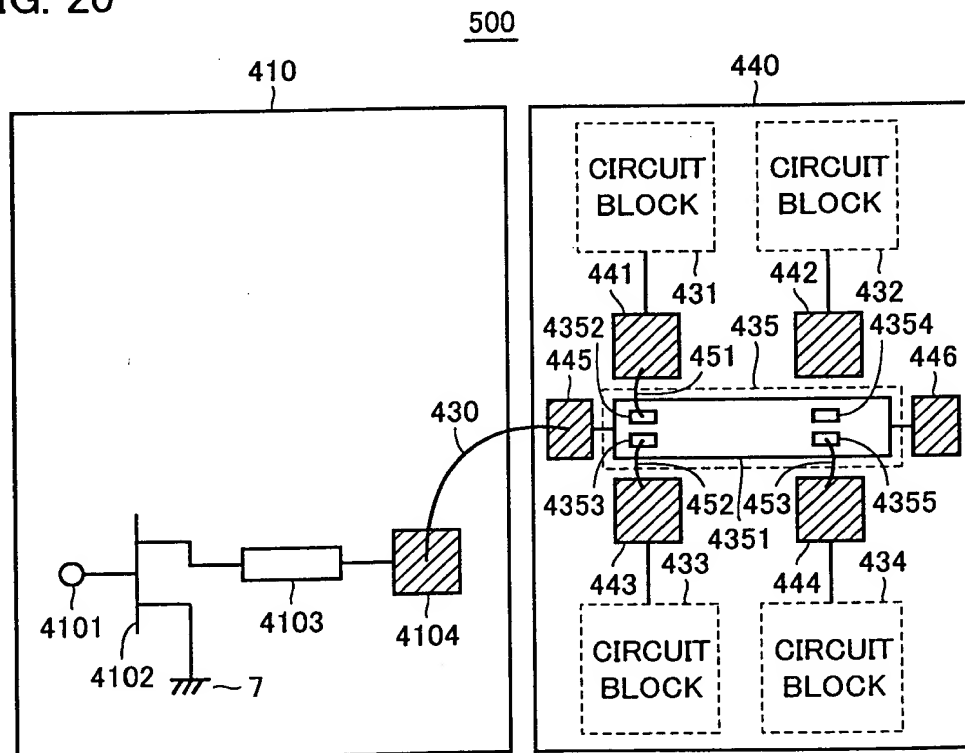


FIG. 21

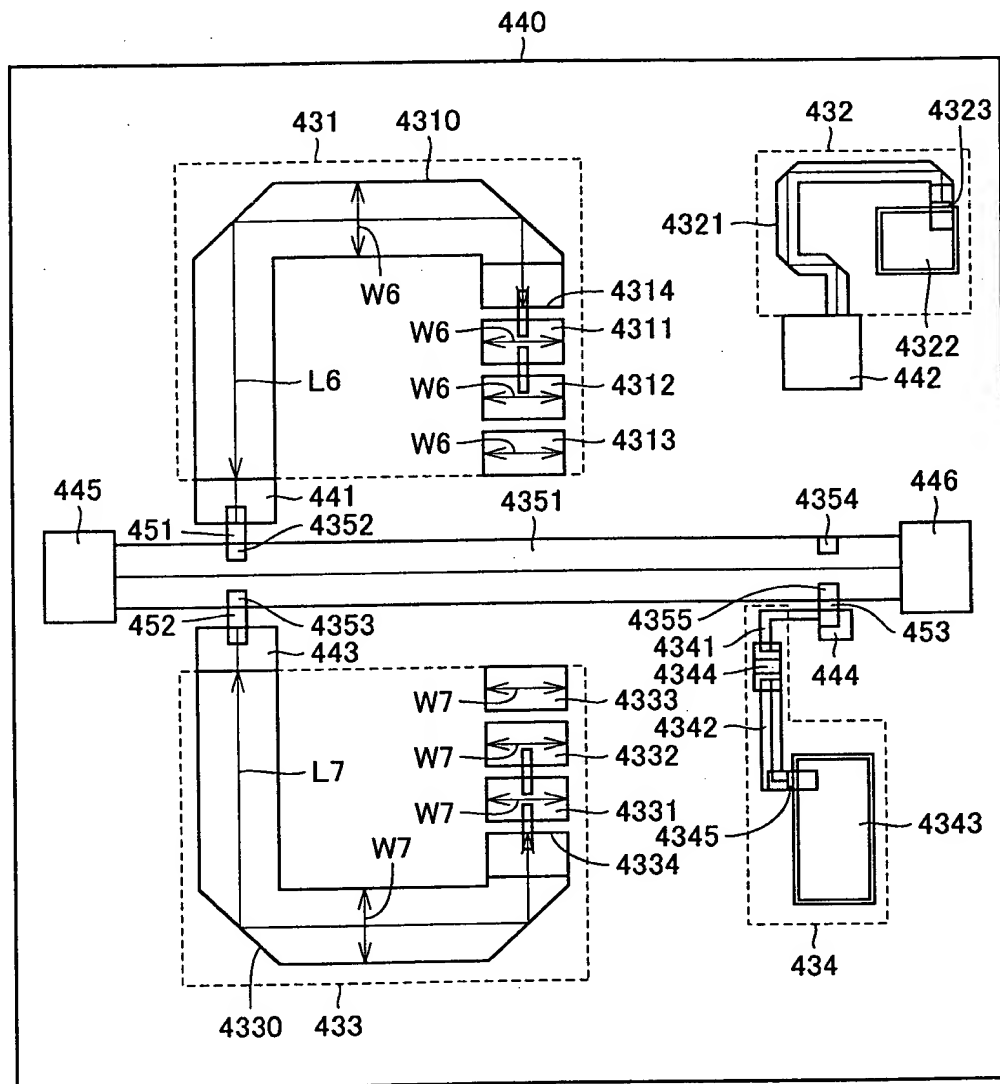


FIG. 22 PRIOR ART

